

NL27WZ06

Dual Inverter with Open Drain Outputs

The NL27WZ06 is a high performance dual inverter with open drain outputs operating from a 1.65 V to 5.5 V supply.

The internal circuit is composed of multiple stages, including an open drain output. The open drain output provides the capability to set the output switching level to a user selectable value with an external resistor and power supply. The logic high output value is set by the external power supply and can be less than, equal or greater than the V_{CC} power supply, provided the voltage supply is less than 5.5 V.

Features

- Extremely High Speed: t_{PD} 2.4 ns (typical) at $V_{CC} = 5$ V
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Over Voltage Tolerant Inputs
- LVTTTL Compatible – Interface Capability With 5 V TTL Logic with $V_{CC} = 3$ V
- LVCMOS Compatible
- 24 mA Output Sink Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Chip Complexity: FET = 72; Equivalent Gate = 18
- These Devices are Pb-Free and are RoHS Compliant
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

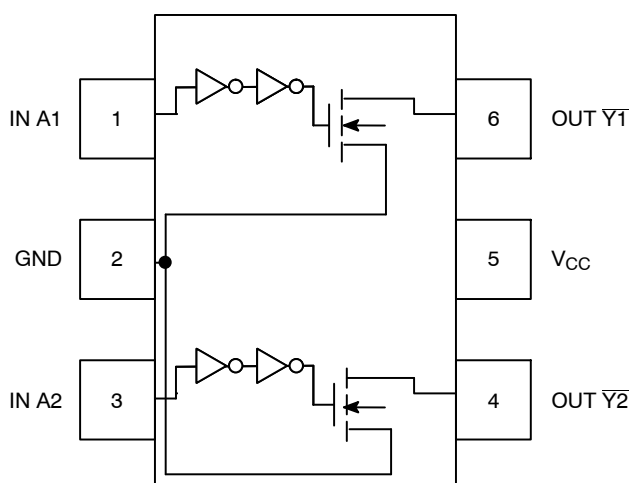


Figure 1. Pinout (Top View)

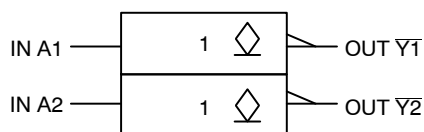


Figure 2. Logic Symbol



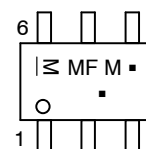
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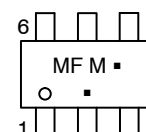
MARKING DIAGRAMS



SC-88
DF SUFFIX
CASE 419B



TSOP-6
DT SUFFIX
CASE 318G



MF = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

Pin	Function
1	IN A1
2	GND
3	IN A2
4	OUT $\bar{Y}2$
5	V_{CC}
6	OUT $\bar{Y}1$

FUNCTION TABLE

A Input	$\bar{Y}$ Output
L	Z
H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Characteristics	Value	Units
V _{CC}	DC Supply Voltage	−0.5 to +7.0	V
V _I	DC Input Voltage	−0.5 ≤ V _I ≤ +7.0	V
V _O	DC Output Voltage Output in Z or LOW State (Note 1)	−0.5 ≤ V _O ≤ 7.0	V
I _{IK}	DC Input Diode Current V _I < GND	−50	mA
I _{OK}	DC Output Diode Current V _O < GND	−50	mA
I _O	DC Output Sink Current	±50	mA
I _{CC}	DC Supply Current Per Supply Pin	±100	mA
I _{GND}	DC Ground Current Per Ground Pin	±100	mA
T _{STG}	Storage Temperature Range	−65 to +150	°C
P _D	Power Dissipation in Still Air SC−88, TSOP−6	200	mW
θ _{JA}	Thermal Resistance SC−88, TSOP−6	333	°C/W
T _L	Lead Temperature, 1 mm from Case for 10 s	260	°C
T _J	Junction Temperature under Bias	+150	°C
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
I _{Latchup}	Latchup Performance Above V _{CC} and Below GND at 85°C (Note 5)	±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I_O absolute maximum rating must be observed.
2. Tested to EIA/JESD22−A114−A
3. Tested to EIA/JESD22−A115−A
4. Tested to JESD22−C101−A
5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Units
V _{CC}	Supply Voltage Operating Data Retention Only	1.65 1.5	5.5 5.5	V
V _I	Input Voltage	0	5.5	V
V _O	Output Voltage (Z or LOW State)	0	5.5	V
T _A	Operating Free−Air Temperature	−55	+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate V _{CC} = 2.5 V ±0.2 V V _{CC} = 3.0 V ±0.3 V V _{CC} = 5.0 V ±0.5 V	0 0 0	20 10 5	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 85°C		Units
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		1.65 2.3 to 5.5	0.75 V _{CC} 0.70 V _{CC}			0.75 V _{CC} 0.70 V _{CC}		V
V _{IL}	Low-Level Input Voltage		1.65 2.3 to 5.5			0.25 V _{CC} 0.30 V _{CC}		0.25 V _{CC} 0.30 V _{CC}	V
I _{LKG}	Z-State Output Leakage Current	V _{IN} = V _{IL} V _{OUT} = V _{CC} or GND	1.65 to 5.5			±5.0		±10.0	μA
V _{OL}	Low-Level Output Voltage V _{IN} = V _{IH}	I _{OL} = 100 μA	1.65 to 5.5		0.0	0.1		0.1	V
		I _{OL} = 3 mA	1.65		0.08	0.24			
		I _{OL} = 8 mA	2.3		0.22	0.3		0.3	
		I _{OL} = 12 mA	2.7		0.22	0.4		0.4	
		I _{OL} = 16 mA	3.0		0.28	0.4		0.4	
		I _{OL} = 24 mA	3.0		0.38	0.55		0.55	
		I _{OL} = 32 mA	4.5		0.42	0.55		0.55	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0			1		10	μA
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5			1		10	μA

AC ELECTRICAL CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 85°C		Units
				Min	Typ	Max	Min	Max	
t _{PZL}	Propagation Delay (Figure 3 and 4)	R _L = R ₁ = 5000 Ω, C _L = 15 pF	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
		R _L = R ₁ = 500 Ω, C _L = 50 pF	2.5 ± 0.20	0.8	3.0	3.6	0.8	4.1	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	3.3 ± 0.30	0.8	2.4	3.2	0.8	3.7	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	5.0 ± 0.50	0.5	2.4	3.0	0.5	3.5	
t _{PLZ}	Propagation Delay (Figure 3 and 4)	R _L = R ₁ = 5000 Ω, C _L = 15 pF	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
		R _L = R ₁ = 500 Ω, C _L = 50 pF	2.5 ± 0.20	0.8	3.0	3.6	0.8	4.1	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	3.3 ± 0.30	0.8	2.1	3.2	0.8	3.7	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	5.0 ± 0.50	0.5	1.2	3.0	0.5	3.5	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	2.5	pF
C _{OUT}	Output Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4	pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-55°C ≤ T _A ≤ 125°C		Units
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		1.65 2.3 to 5.5	0.75 V _{CC} 0.70 V _{CC}			0.75 V _{CC} 0.70 V _{CC}		V
V _{IL}	Low-Level Input Voltage		1.65 2.3 to 5.5			0.25 V _{CC} 0.30 V _{CC}		0.25 V _{CC} 0.30 V _{CC}	V
I _{LKG}	Z-State Output Leakage Current	V _{IN} = V _{IL} V _{OUT} = V _{CC} or GND	1.65 to 5.5			±5.0		±10.0	μA
V _{OL}	Low-Level Output Voltage V _{IN} = V _{IH}	I _{OL} = 100 μA	1.65 to 5.5		0.0	0.1		0.1	V
		I _{OL} = 3 mA	1.65		0.08	0.24			
		I _{OL} = 8 mA	2.3		0.22	0.3		0.35	
		I _{OL} = 12 mA	2.7		0.22	0.4		0.45	
		I _{OL} = 16 mA	3.0		0.28	0.4		0.5	
		I _{OL} = 24 mA	3.0		0.38	0.55		0.65	
		I _{OL} = 32 mA	4.5		0.42	0.55		0.65	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0			1		10	μA
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5			1		10	μA

AC ELECTRICAL CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-55°C ≤ T _A ≤ 125°C		Units
				Min	Typ	Max	Min	Max	
t _{PZL}	Propagation Delay (Figure 3 and 4)	R _L = R ₁ = 5000 Ω, C _L = 15 pF	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
		R _L = R ₁ = 500 Ω, C _L = 50 pF	2.5 ± 0.20	0.8	3.0	3.6	0.8	4.1	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	3.3 ± 0.30	0.8	2.4	3.2	0.8	3.7	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	5.0 ± 0.50	0.5	2.4	3.0	0.5	3.5	
t _{PLZ}	Propagation Delay (Figure 3 and 4)	R _L = R ₁ = 5000 Ω, C _L = 15 pF	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
		R _L = R ₁ = 500 Ω, C _L = 50 pF	2.5 ± 0.20	0.8	3.8	4.5	0.8	5.0	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	3.3 ± 0.30	0.8	2.9	3.2	0.8	3.7	
		R _L = R ₁ = 500 Ω, C _L = 50 pF	5.0 ± 0.50	0.5	1.2	3.0	0.5	3.5	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	2.5	pF
C _{OUT}	Output Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4	pF

7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NL27WZ06

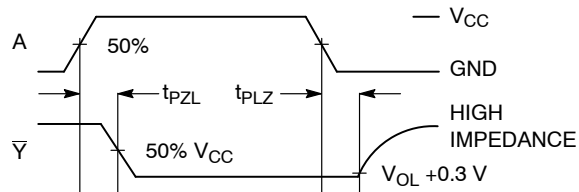


Figure 3. Switching Waveforms

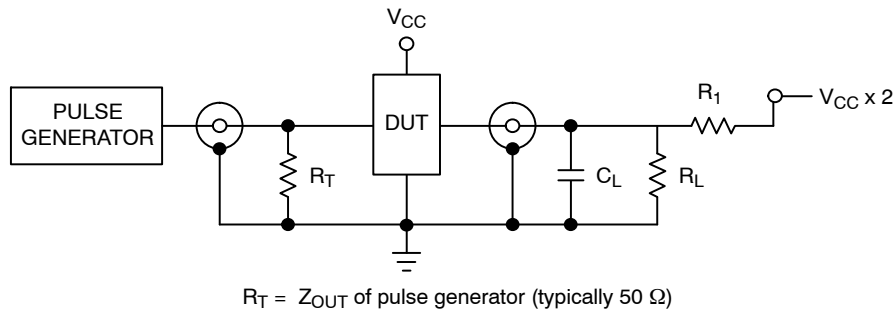


Figure 4. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
NL27WZ06DFT2G	SC-88 (Pb-Free)	3000 / Tape & Reel
NLV27WZ06DFT2G*	SC-88 (Pb-Free)	3000 / Tape & Reel
NL27WZ06DTT1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

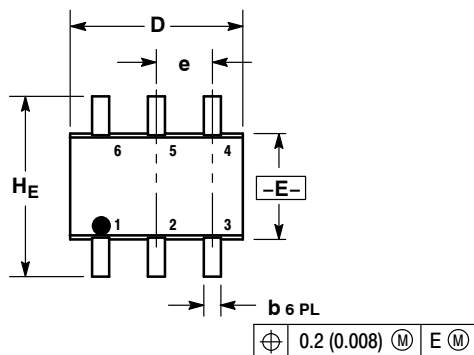
NL27WZ06

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02

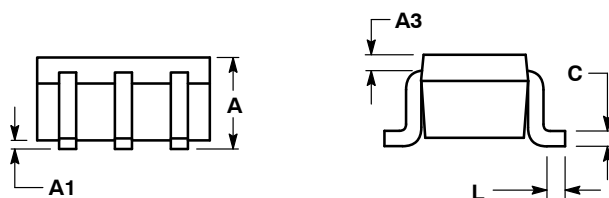
ISSUE W



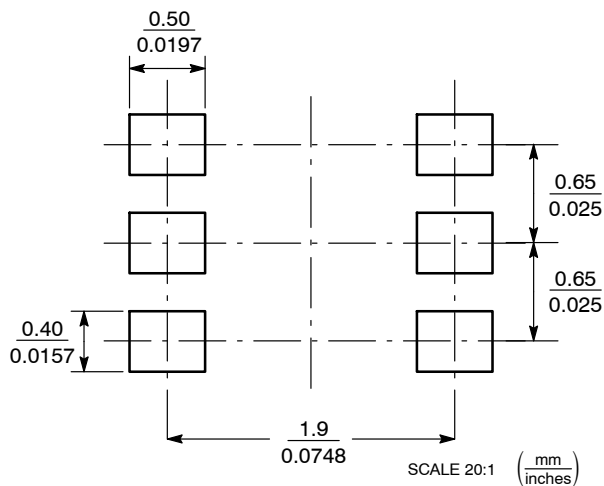
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086



SOLDERING FOOTPRINT*

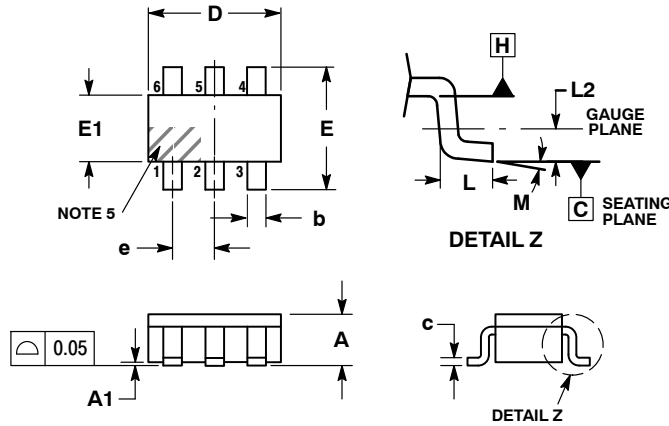


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NL27WZ06

PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE U

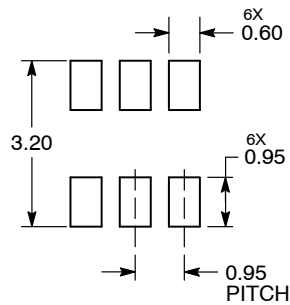


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	-	10°

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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